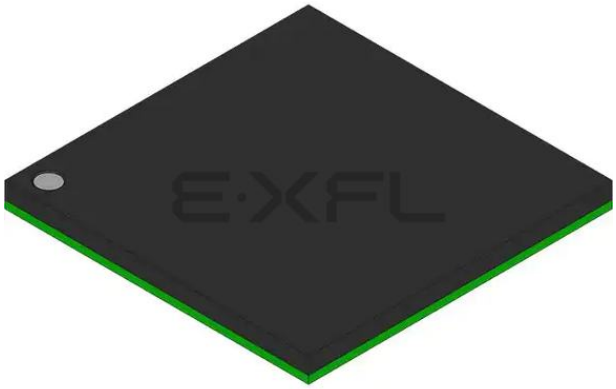

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1.3 Block Diagram

Figure 1 shows the MCIMX31 simplified interface block diagram.

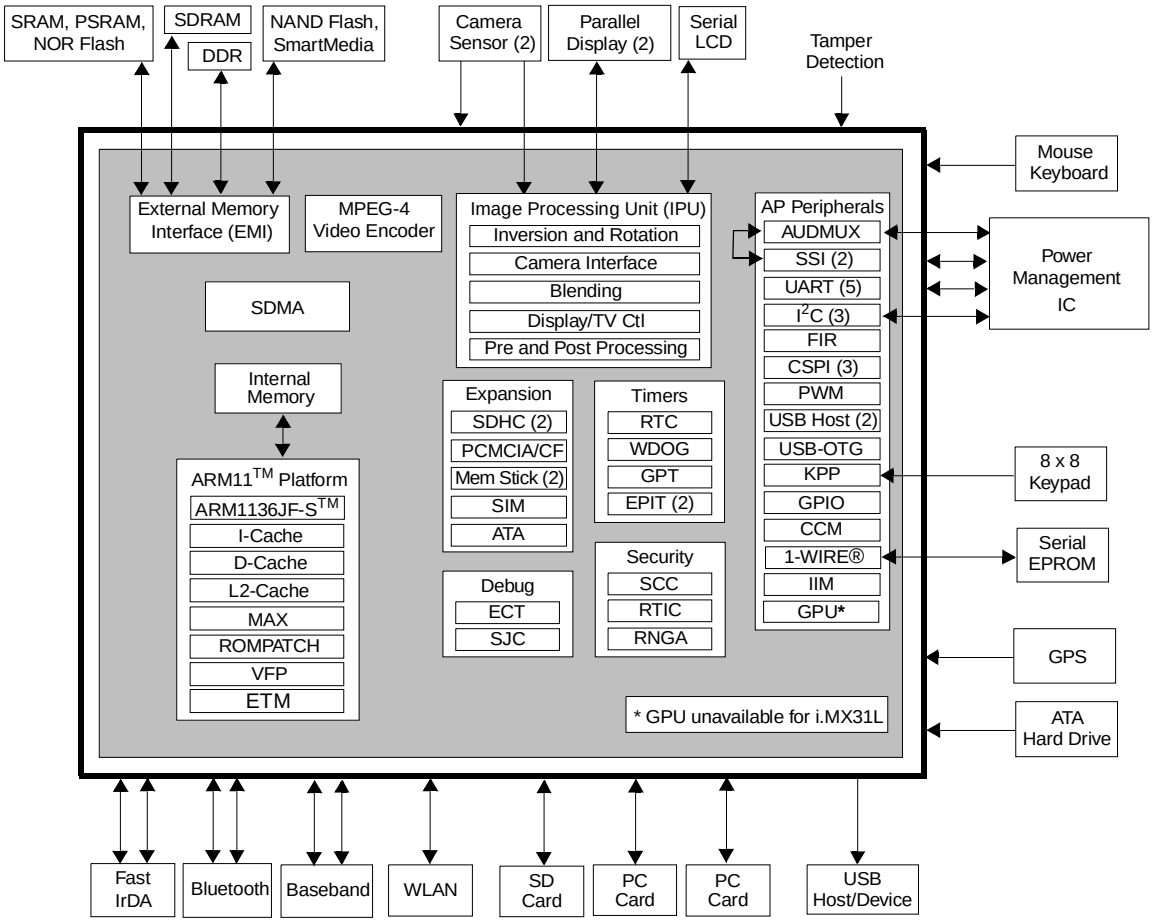


Figure 1. MCIMX31 Simplified Interface Block Diagram

2 Functional Description and Application Information

2.1 ARM11 Microprocessor Core

The CPU of the MCIMX31 is the ARM1136JF-S core based on the ARM v6 architecture. It supports the ARM Thumb® instruction sets, features Jazelle® technology (which enables direct execution of Java byte codes), and a range of SIMD DSP instructions that operate on 16-bit or 8-bit data values in 32-bit registers.

The ARM1136JF-S processor core features:

- Integer unit with integral EmbeddedICE™ logic
- Eight-stage pipeline
- Branch prediction with return stack
- Low-interrupt latency

Table 13 shows the core current consumption for –20°C to 70°C for Silicon Revision 2.0.1 for the MCIMX31.

Table 13. Current Consumption for –20°C to 70°C[1, 2] for Silicon Revision 2.0.1

Mode	Conditions	QVCC (Peripheral)		QVCC1 (ARM)		QVCC4 (L2)		FVCC, +MVCC, +SVCC, +UVCC (PLL)		Unit
		Typ	Max	Typ	Max	Typ	Max	Typ	Max	
Deep Sleep	• QVCC = 0.95 V • ARM and L2 caches are power gated (QVCC1 2= QVCC4 = 0 V) • All PLLs are off, VCC = 1.4 V • ARM is in well bias • FPM is off • 32 kHz input is on • CKIH input is off • CAMP is off • TCK input is off • All modules are off • No external resistive loads • RNGA oscillator is off	0.16	—	—	—	—	—	0.02	—	mA
State Retention	• QVCC and QVCC1 = 0.95 V • L2 caches are power gated (QVCC4 = 0 V) • All PLLs are off, VCC = 1.4 V • ARM is in well bias • FPM is off • 32 kHz input is on • CKIH input is off • CAMP is off • TCK input is off • All modules are off • No external resistive loads • RNGA oscillator is off	0.16	—	0.07	—	—	—	0.02	—	mA
Wait	• QVCC,QVCC1, and QVCC4 = 1.22 V • ARM is in wait for interrupt mode • MAX is active • L2 cache is stopped but powered • MCU PLL is on (532 MHz), VCC = 1.4 V • USB PLL and SPLL are off, VCC = 1.4 V • FPM is on • CKIH input is on • CAMP is on • 32 kHz input is on • All clocks are gated off • All modules are off (by programming CGR[2:0] registers) • RNGA oscillator is off • No external resistive loads	6.00	—	2.20	—	0.03	—	3.60	—	mA

1 Typical column: TA = 25°C

2 Maximum column: TA = 70°C

Table 14. GPIO DC Electrical Parameters (continued)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Low-level output current, fast slew rate	I_{OL_F}	V_{OL}=0.2*NVCC Std Drive High Drive Max Drive	 4 6 8	—	—	mA
High-Level DC input voltage	V_{IH}	—	0.7*NVCC	—	NVCC	V
Low-Level DC input voltage	V_{IL}	—	0	—	0.3*QVCC	V
Input Hysteresis	V_{HYS}	Hysteresis enabled	0.25	—	—	V
Schmitt trigger VT+	V_T +	Hysteresis enabled	0.5*QVCC	—	—	V
Schmitt trigger VT–	V_T –	Hysteresis enabled	—	—	0.5*QVCC	V
Pull-up resistor (100 kΩ PU)	R_{PU}	—	—	100	—	kΩ
Pull-down resistor (100 kΩ PD)	R_{PD}	—	—	100	—	
Input current (no PU/PD)	I_{IN}	V_I = NVCC or GND	—	—	±1	µA
Input current (100 kΩ PU)	I_{IN}	V_I = 0 V_I = NVCC	—	—	25 0.1	µA µA
Input current (100 kΩ PD)	I_{IN}	V_I = 0 V_I = NVCC	—	—	0.25 28	µA µA
Tri-state leakage current	I_{OZ}	V_I = NVCC or GND I/O = High Z	—	—	±2	µA

The MCIMX31 I/O parameters appear in Table 15 for DDR (Double Data Rate). See Table 8, "Operating Ranges," on page 13 for temperature and supply voltage ranges.

NOTE

NVCC for Table 15 refers to NVCC2, NVCC21, and NVCC22.

Table 15. DDR (Double Data Rate) I/O DC Electrical Parameters

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
High-level output voltage	V_{OH}	I_{OH} = –1 mA	NVCC –0.12	—	—	V
		I_{OH} = specified Drive	0.8*NVCC	—	—	V
Low-level output voltage	V_{OL}	I_{OL} = 1 mA	—	—	0.08	V
		I_{OL} = specified Drive	—	—	0.2*NVCC	V
High-level output current	I_{OH}	V_{OH}=0.8*NVCC Std Drive High Drive Max Drive DDR Drive[1]	 –3.6 –7.2 –10.8 –14.4	—	—	mA
Low-level output current	I_{OL}	V_{OL}=0.2*NVCC Std Drive High Drive Max Drive DDR Drive[1]	 3.6 7.2 10.8 14.4	—	—	mA

Table 17. AC Electrical Characteristics of Fast[1] General I/O [2]

ID	Parameter	Symbol	Test Condition	Min	Typ	Max	Units
PA1	Output Transition Times (Max Drive)	tpr	25 pF 50 pF	0.68 1.34	1.33 2.6	2.07 4.06	ns
	Output Transition Times (High Drive)	tpr	25 pF 50 pF	.91 1.79	1.77 3.47	2.74 5.41	ns
	Output Transition Times (Std Drive)	tpr	25 pF 50 pF	1.36 2.68	2.64 5.19	4.12 8.11	ns

1 Fast/slow characteristic is selected per GPIO (where available) by “slew rate” control. See reference manual.

2 Use of GPIO in fast mode with the associated NVCC > 1.95 V can result in excessive overshoot and ringing.

Table 18. AC Electrical Characteristics of DDR I/O

ID	Parameter	Symbol	Test Condition	Min	Typ	Max	Units
PA1	Output Transition Times (DDR Drive)[1]	tpr	25 pF 50 pF	0.51 0.97	0.82 1.58	1.28 2.46	ns
	Output Transition Times (Max Drive)	tpr	25 pF 50 pF	0.67 1.29	1.08 2.1	1.69 3.27	ns
	Output Transition Times (High Drive)	tpr	25 pF 50 pF	.99 1.93	1.61 3.13	2.51 4.89	ns
	Output Transition Times (Std Drive)	tpr	25 pF 50 pF	1.96 3.82	3.19 6.24	4.99 9.73	ns

1 Use of DDR Drive can result in excessive overshoot and ringing.

4.3.3 Clock Amplifier Module (CAMP) Electrical Characteristics

This section outlines the Clock Amplifier Module (CAMP) specific electrical characteristics. Table 19 shows clock amplifier electrical characteristics.

Table 19. Clock Amplifier Electrical Characteristics for CKIH Input

Parameter	Min	Typ	Max	Units
Input Frequency	15	—	75	MHz
VIL (for square wave input)	0	—	0.3	V
VIH (for square wave input)	(VDD [1]– 0.25)	—	3	V
Sinusoidal Input Amplitude	0.4 [2]	—	VDD	Vp-p
Duty Cycle	45	50	55	%

1 VDD is the supply voltage of CAMP. See reference manual.

2 This value of the sinusoidal input will be measured through characterization.

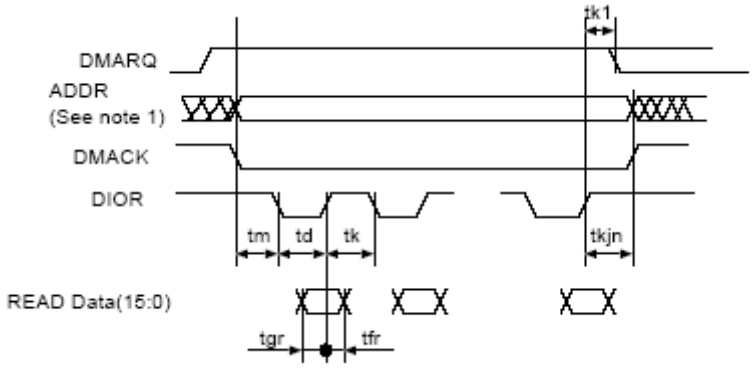


Figure 12. MDMA Read Timing Diagram

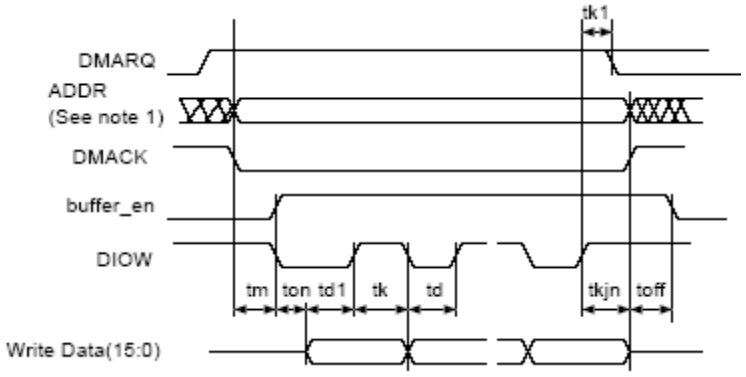


Figure 13. MDMA Write Timing Diagram

Table 26. MDMA Read and Write Timing Parameters

ATA Parameter	Parameter from Figure 12, Figure 13	Value	Controlling Variable
tm, ti	tm	tm (min) = ti (min) = time_m * T – (tskew1 + tskew2 + tskew5)	time_m
td	td, td1	td1.(min) = td (min) = time_d * T – (tskew1 + tskew2 + tskew6)	time_d
tk	tk	tk.(min) = time_k * T – (tskew1 + tskew2 + tskew6)	time_k
t0	—	t0 (min) = (time_d + time_k) * T	time_d, time_k
tg(read)	tgr	tgr (min-read) = tco + tsu + tbuf + tbuf + tcable1 + tcable2 tgr.(min-drive) = td – te(drive)	time_d
tf(read)	tfr	tfr (min-drive) = 0	—
tg(write)	—	tg (min-write) = time_d * T – (tskew1 + tskew2 + tskew5)	time_d
tf(write)	—	tf (min-write) = time_k * T – (tskew1 + tskew2 + tskew6)	time_k
tL	—	tL (max) = (time_d + time_k–2)*T – (tsu + tco + 2*tbuf + 2*tcable2)	time_d, time_k
tn, tj	tkjn	tn= tj= tkjn = (max(time_k,. time_jn) * T – (tskew1 + tskew2 + tskew6)	time_jn
—	ton toff	ton = time_on * T – tskew1 toff = time_off * T – tskew1	—

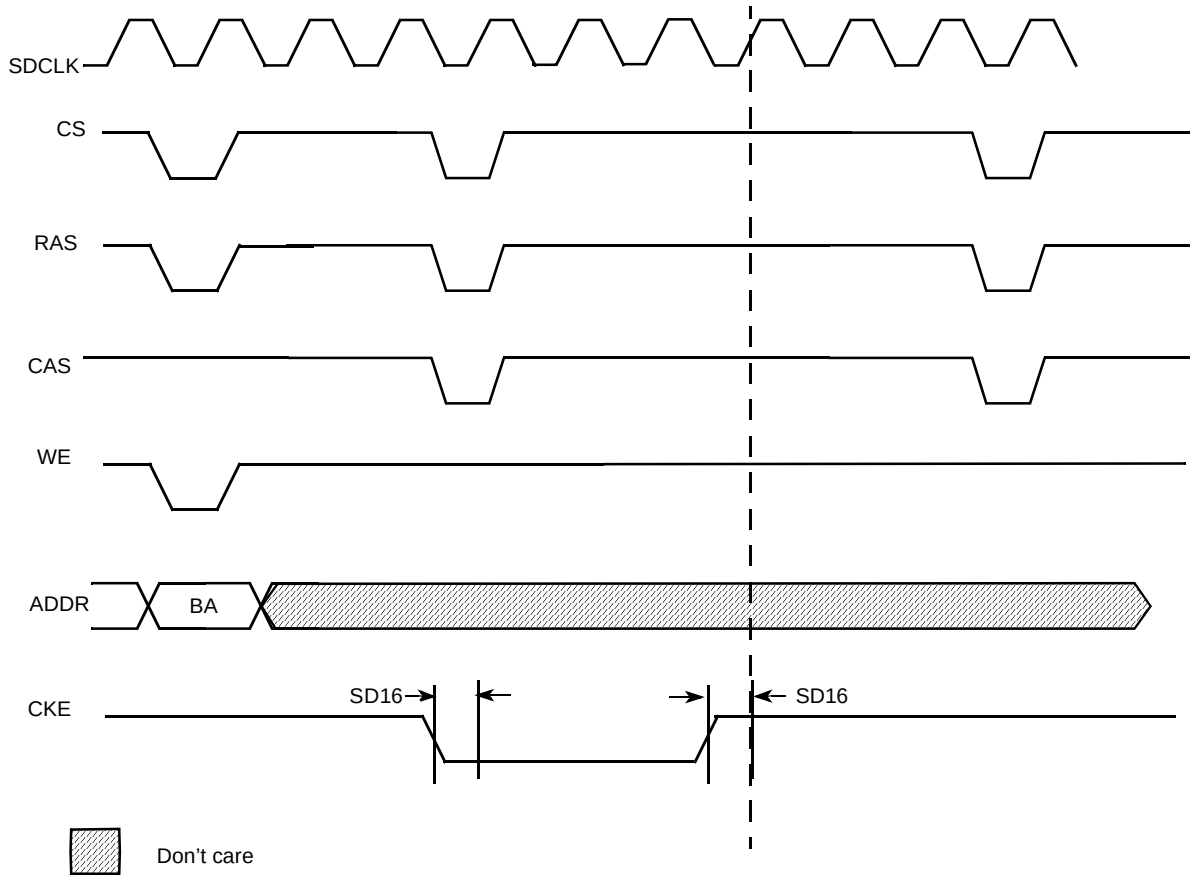


Figure 36. SDRAM Self-Refresh Cycle Timing Diagram

NOTE

The clock will continue to run unless both CKEs are low. Then the clock will be stopped in low state.

Table 36. SDRAM Self-Refresh Cycle Timing Parameters

ID	Parameter	Symbol	Min	Max	Unit
SD16	CKE output delay time	tCKS	1.8	—	ns

NOTE

HSP_CLK is the High-Speed Port Clock, which is the input to the Image Processing Unit (IPU). Its frequency is controlled by the Clock Control Module (CCM) settings. The HSP_CLK frequency must be greater than or equal to the AHB clock frequency.

The SCREEN_WIDTH, SCREEN_HEIGHT, H_SYNC_WIDTH, V_SYNC_WIDTH, BGXP, BGYP and V_SYNC_WIDTH_L parameters are programmed via the SDC_HOR_CONF, SDC_VER_CONF, SDC_BG_POS Registers. The FW and FH parameters are programmed for the corresponding DMA channel. The DISP3_IF_CLK_PER_WR, HSP_CLK_PERIOD and DISP3_IF_CLK_CNT_D parameters are programmed via the DI_DISP3_TIME_CONF, DI_HSP_CLK_PER and DI_DISP_ACC_CC Registers.

Figure 48 depicts the synchronous display interface timing for access level, and Table 47 lists the timing parameters. The DISP3_IF_CLK_DOWN_WR and DISP3_IF_CLK_UP_WR parameters are set via the DI_DISP3_TIME_CONF Register.

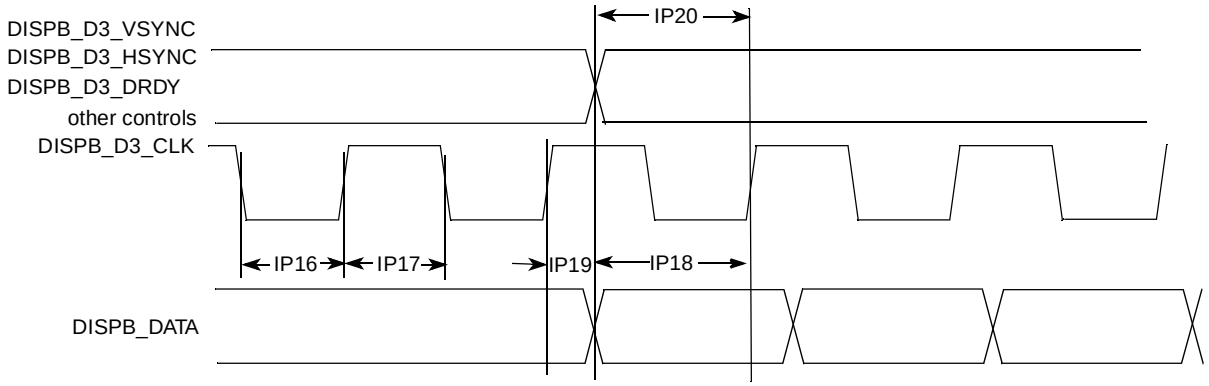


Figure 48. Synchronous Display Interface Timing Diagram—Access Level

Table 47. Synchronous Display Interface Timing Parameters—Access Level

ID	Parameter	Symbol	Min	Typ[1]	Max	Units
IP16	Display interface clock low time	Tckl	Tdicd–Tdicu–1.5	Tdicd[2]–Tdicu[3]	Tdicd–Tdicu+1.5	ns
IP17	Display interface clock high time	Tckh	Tdicp–Tdicd+Tdicu–1.5	Tdicp–Tdicd+Tdicu	Tdicp–Tdicd+Tdicu+1.5	ns
IP18	Data setup time	Tdsu	Tdicd–3.5	Tdicu	—	ns
IP19	Data holdup time	Tdhd	Tdicp–Tdicd–3.5	Tdicp–Tdicu	—	ns
IP20	Control signals setup time to display interface clock	Tcsu	Tdicd–3.5	Tdicu	—	ns

1 The exact conditions have not been finalized, but will likely match the current customer requirement for their specific display. These conditions may be device specific.

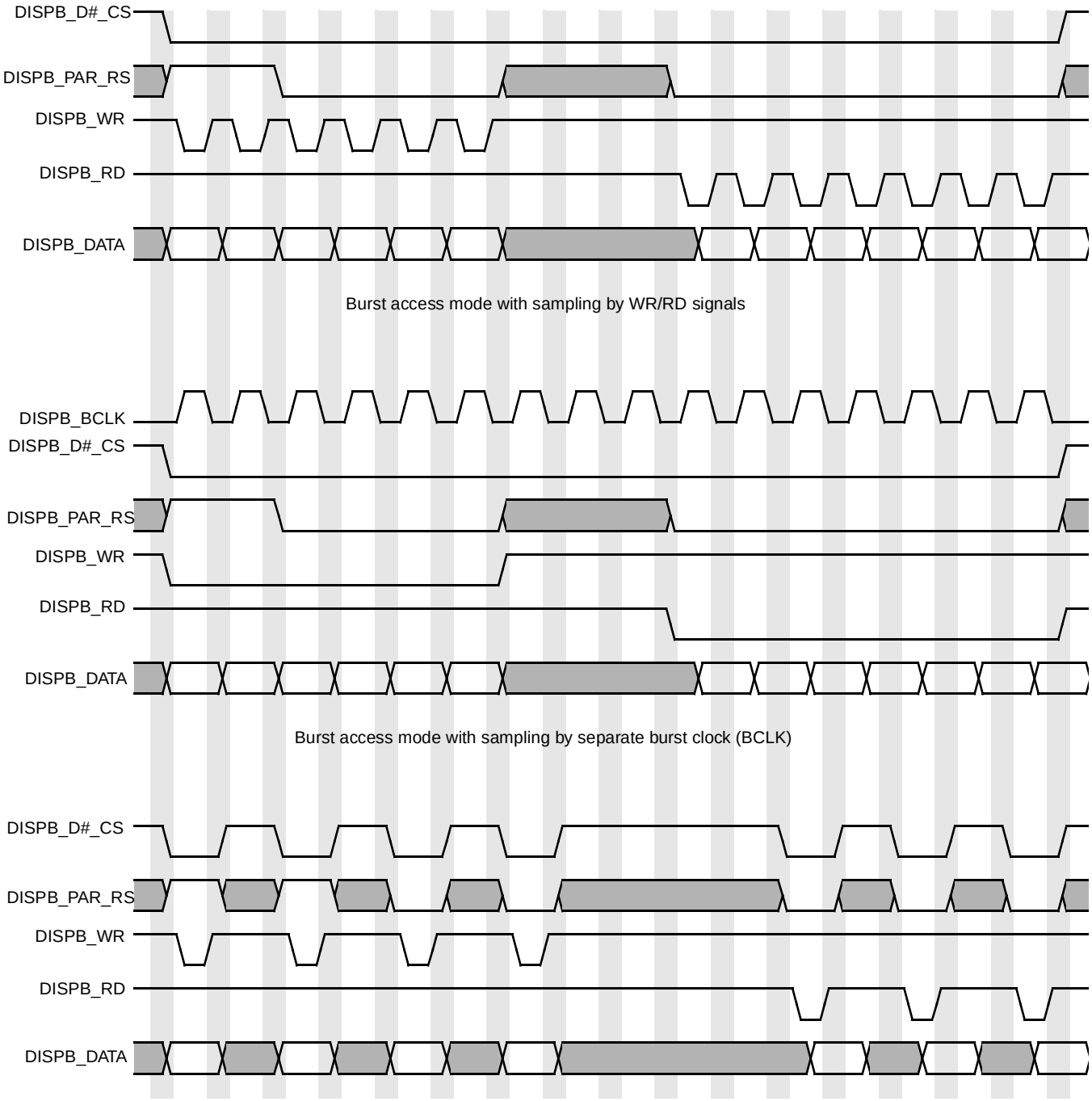


Figure 52. Asynchronous Parallel System 80 Interface (Type 2) Burst Mode Timing Diagram

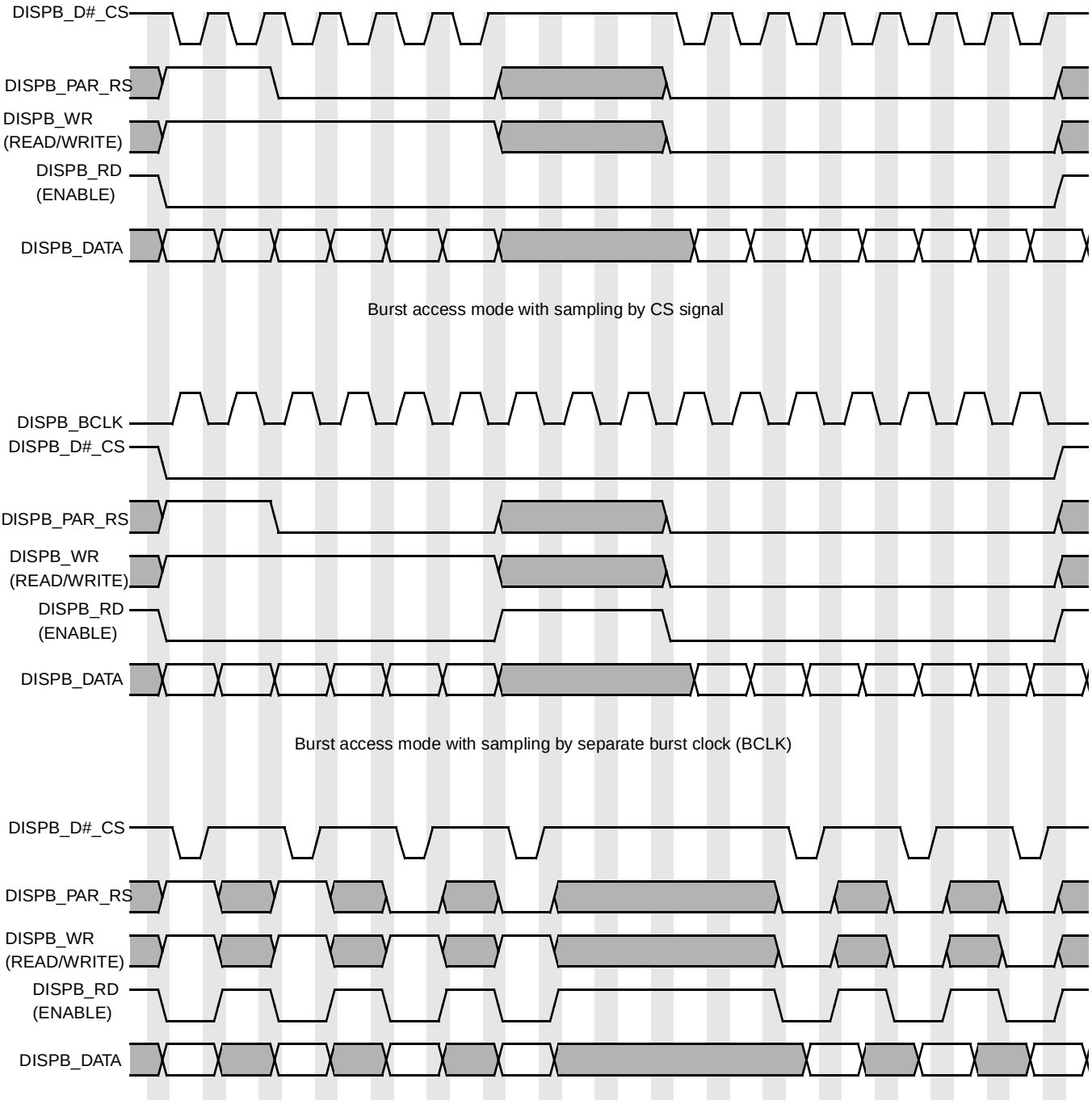


Figure 53. Asynchronous Parallel System 68k Interface (Type 1) Burst Mode Timing Diagram

Table 49. Asynchronous Parallel Interface Timing Parameters—Access Level (continued)

ID	Parameter	Symbol	Min.	Typ.[1]	Max.	Units
IP36	Controls hold time for write	Tdchw	Tdicpw–Tdicdw–1.5	Tdicpw–Tdicdw	—	ns
IP37	Slave device data delay[8]	Tracc	0	—	Tdrp[9]–Tlbd[10]–Tdicur–1.5	ns
IP38	Slave device data hold time[8]	Troh	Tdrp–Tlbd–Tdicdr+1.5	—	Tdicpr–Tdicdr–1.5	ns
IP39	Write data setup time	Tds	Tdicdw–1.5	Tdicdw	—	ns
IP40	Write data hold time	Tdh	Tdicpw–Tdicdw–1.5	Tdicpw–Tdicdw	—	ns
IP41	Read period[2]	Tdicpr	Tdicpr–1.5	Tdicpr	Tdicpr+1.5	ns
IP42	Write period[3]	Tdicpw	Tdicpw–1.5	Tdicpw	Tdicpw+1.5	ns
IP43	Read down time[4]	Tdicdr	Tdicdr–1.5	Tdicdr	Tdicdr+1.5	ns
IP44	Read up time[5]	Tdicur	Tdicur–1.5	Tdicur	Tdicur+1.5	ns
IP45	Write down time[6]	Tdicdw	Tdicdw–1.5	Tdicdw	Tdicdw+1.5	ns
IP46	Write up time[7]	Tdicuw	Tdicuw–1.5	Tdicuw	Tdicuw+1.5	ns
IP47	Read time point[9]	Tdrp	Tdrp–1.5	Tdrp	Tdrp+1.5	ns

[1]The exact conditions have not been finalized, but will likely match the current customer requirement for their specific display. These conditions may be device specific.

[2] Display interface clock period value for read:

$$Tdicpr = T_{HSP\_CLK} \cdot ceil\left[\frac{DISP\#\_IF\_CLK\_PER\_RD}{HSP\_CLK\_PERIOD}\right]$$

[3] Display interface clock period value for write:

$$Tdicpw = T_{HSP\_CLK} \cdot ceil\left[\frac{DISP\#\_IF\_CLK\_PER\_WR}{HSP\_CLK\_PERIOD}\right]$$

[4] Display interface clock down time for read:

$$Tdicdr = \frac{1}{2}T_{HSP\_CLK} \cdot ceil\left[\frac{2 \cdot DISP\#\_IF\_CLK\_DOWN\_RD}{HSP\_CLK\_PERIOD}\right]$$

[5] Display interface clock up time for read:

$$Tdicur = \frac{1}{2}T_{HSP\_CLK} \cdot ceil\left[\frac{2 \cdot DISP\#\_IF\_CLK\_UP\_RD}{HSP\_CLK\_PERIOD}\right]$$

[6] Display interface clock down time for write:

$$Tdicdw = \frac{1}{2}T_{HSP\_CLK} \cdot ceil\left[\frac{2 \cdot DISP\#\_IF\_CLK\_DOWN\_WR}{HSP\_CLK\_PERIOD}\right]$$

[7] Display interface clock up time for write:

$$Tdicuw = \frac{1}{2}T_{HSP\_CLK} \cdot ceil\left[\frac{2 \cdot DISP\#\_IF\_CLK\_UP\_WR}{HSP\_CLK\_PERIOD}\right]$$

[8] This parameter is a requirement to the display connected to the IPU

[9] Data read point

$$Tdrp = T_{HSP\_CLK} \cdot ceil\left[\frac{DISP\#\_READ\_EN}{HSP\_CLK\_PERIOD}\right]$$

[10] Loopback delay Tlbd is the cumulative propagation delay of read controls and read data. It includes an IPU output delay, a device-level output delay, board delays, a device-level input delay, an IPU input delay. This value is device specific.

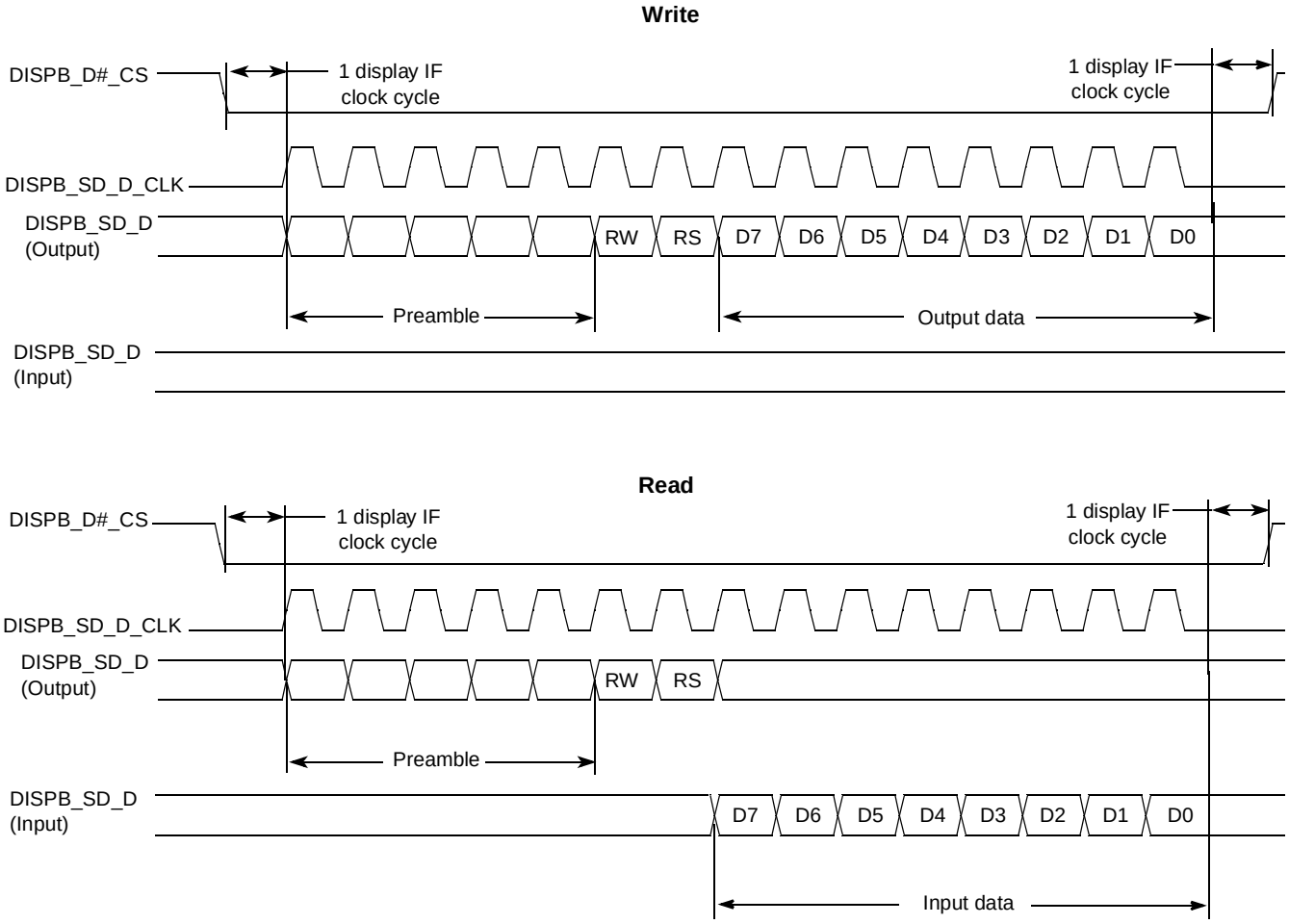


Figure 61. 4-Wire Serial Interface Timing Diagram

Figure 62 depicts timing of the 5-wire serial interface (Type 1). For this interface, a separate RS line is added. When a burst is transmitted within single active chip select interval, the RS can be changed at boundaries of words.

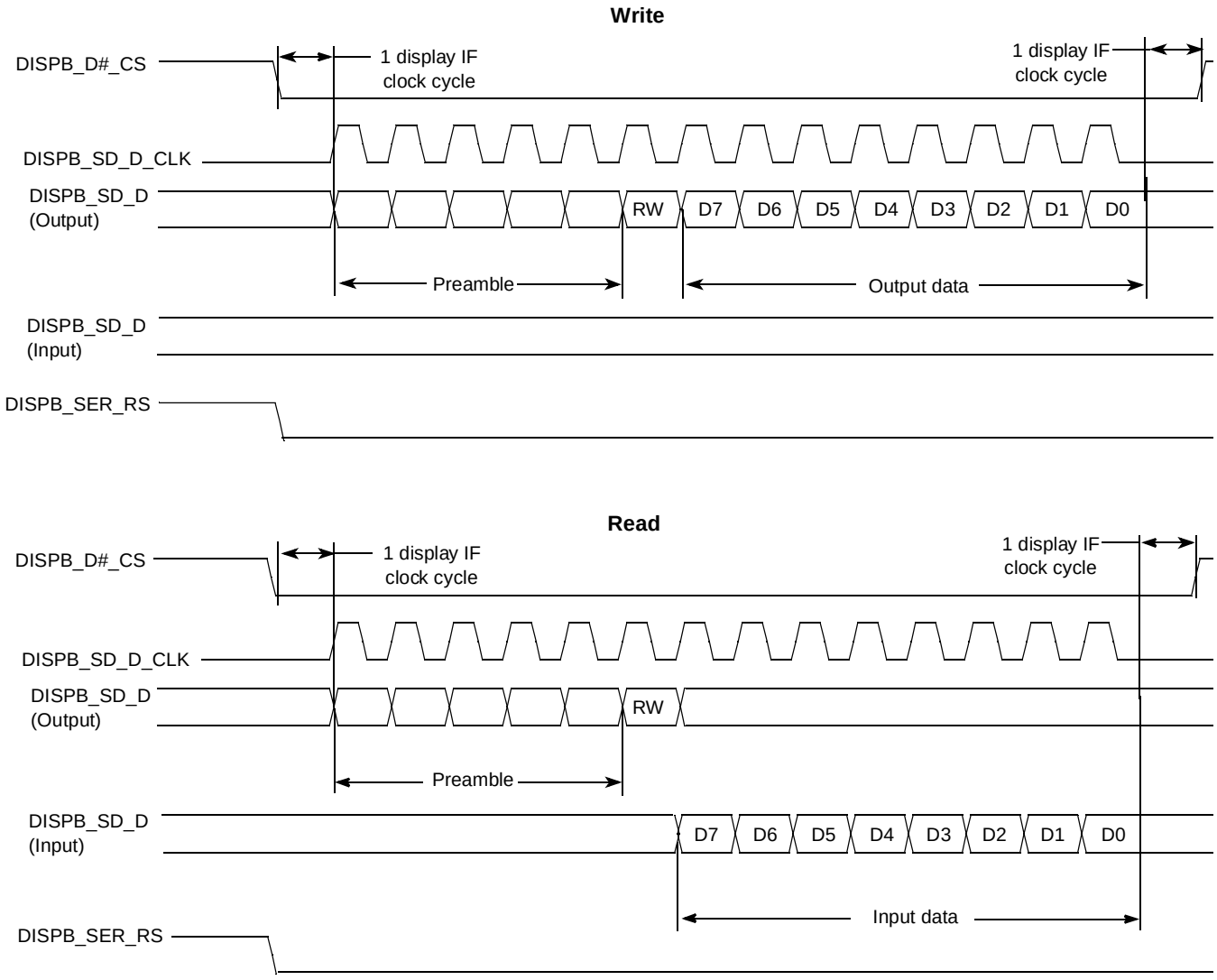


Figure 62. 5-Wire Serial Interface (Type 1) Timing Diagram

4.3.18.1 PWM Timing

Figure 70 depicts the timing of the PWM, and Table 54 lists the PWM timing characteristics.

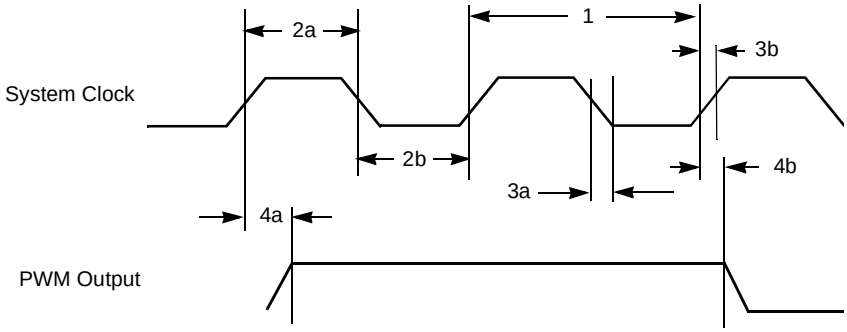


Figure 70. PWM Timing

Table 54. PWM Output Timing Parameters

ID	Parameter	Min	Max	Unit
1	System CLK frequency[1]	0	ipg_clk	MHz
2a	Clock high time	12.29	—	ns
2b	Clock low time	9.91	—	ns
3a	Clock fall time	—	0.5	ns
3b	Clock rise time	—	0.5	ns
4a	Output delay time	—	9.37	ns
4b	Output setup time	8.71	—	ns

[1] CL of PWMO = 30 pF

4.3.19 SDHC Electrical Specifications

This section describes the electrical information of the SDHC.

4.3.19.1 SDHC Timing

Figure 71 depicts the timings of the SDHC, and Table 55 lists the timing parameters.

4.3.21 SJC Electrical Specifications

This section details the electrical characteristics for the SJC module. Figure 76 depicts the SJC test clock input timing. Figure 77 depicts the SJC boundary scan timing, Figure 78 depicts the SJC test access port, Figure 79 depicts the SJC $\overline{\text{TRST}}$ timing, and Table 58 lists the SJC timing parameters.

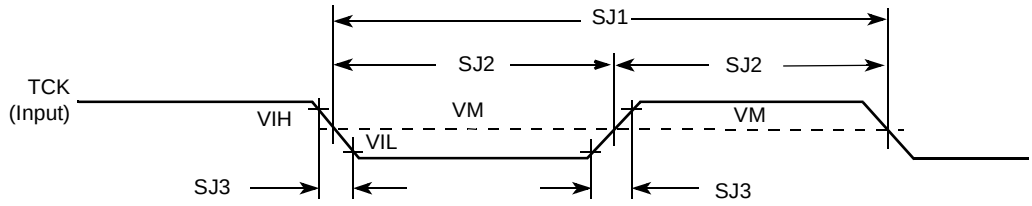


Figure 76. Test Clock Input Timing Diagram

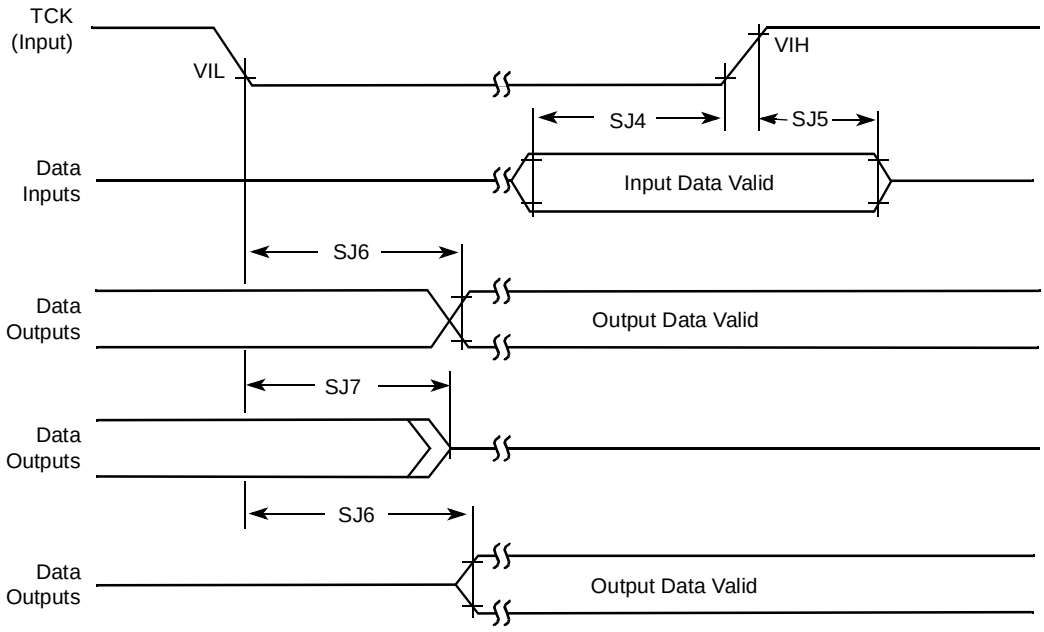


Figure 77. Boundary Scan (JTAG) Timing Diagram

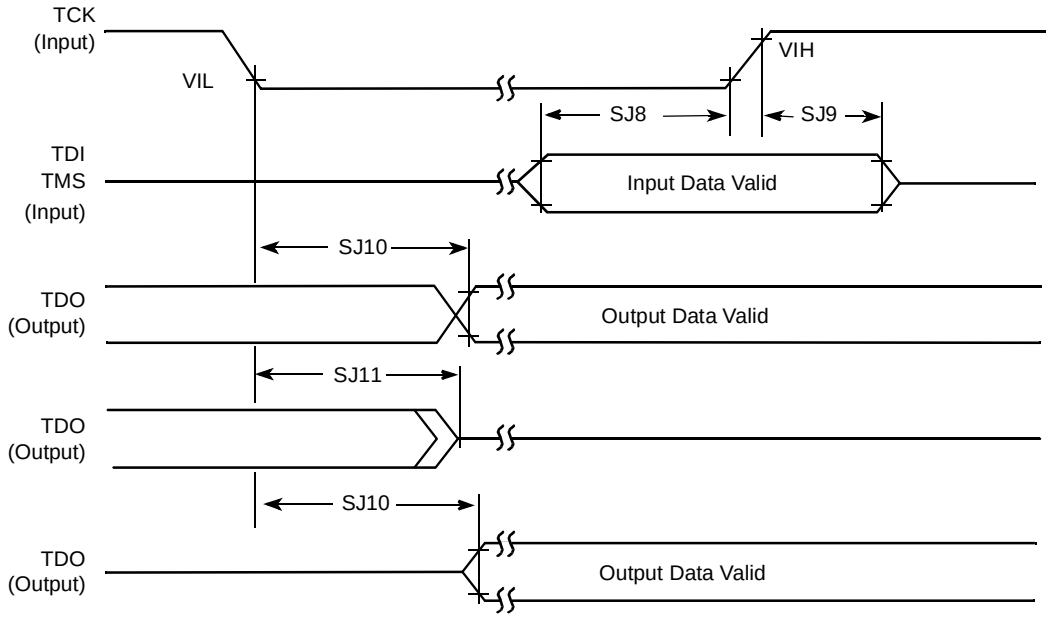


Figure 78. Test Access Port Timing Diagram

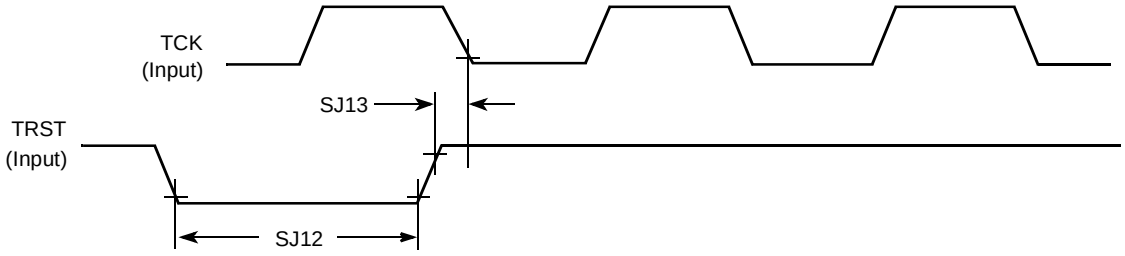
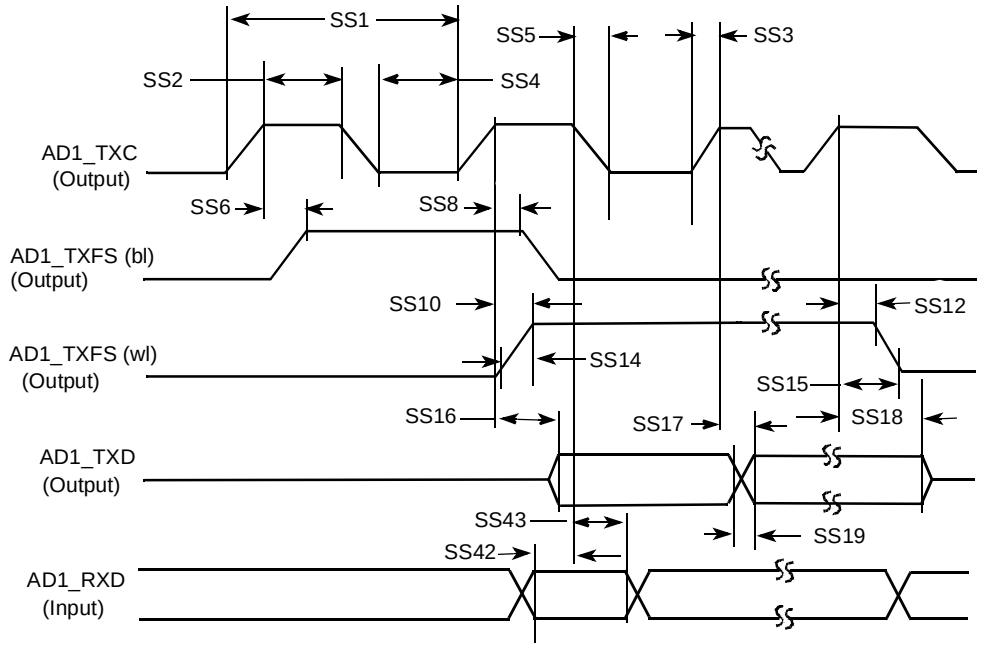


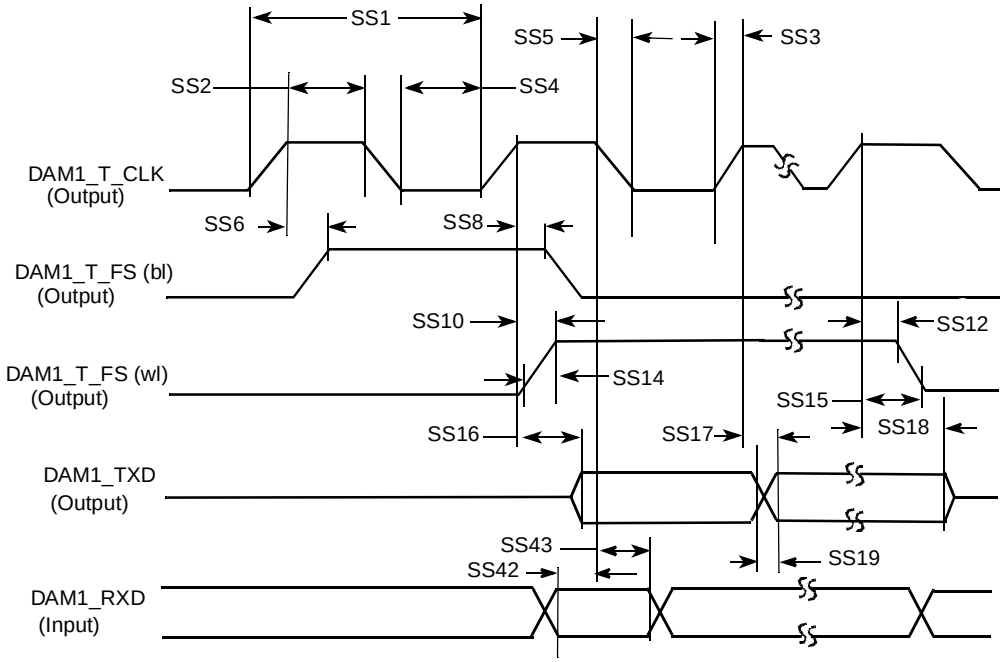
Figure 79. $\overline{\text{TRST}}$ Timing Diagram

Table 58. SJC Timing Parameters

ID	Parameter	All Frequencies		Unit
		Min	Max	
SJ1	TCK cycle time	100[1]	—	ns
SJ2	TCK clock pulse width measured at V_M[2]	40	—	ns
SJ3	TCK rise and fall times	—	3	ns
SJ4	Boundary scan input data set-up time	10	—	ns
SJ5	Boundary scan input data hold time	50	—	ns
SJ6	TCK low to output data valid	—	50	ns
SJ7	TCK low to output high impedance	—	50	ns
SJ8	TMS, TDI data set-up time	10	—	ns
SJ9	TMS, TDI data hold time	50	—	ns
SJ10	TCK low to TDO data valid	—	44	ns



Note: SRXD Input in Synchronous mode only



Note: SRXD Input in Synchronous mode only

Figure 80. SSI Transmitter with Internal Clock Timing Diagram

4.3.22.4 SSI Receiver Timing with External Clock

Figure 83 depicts the SSI receiver timing with external clock, and Table 62 lists the timing parameters.

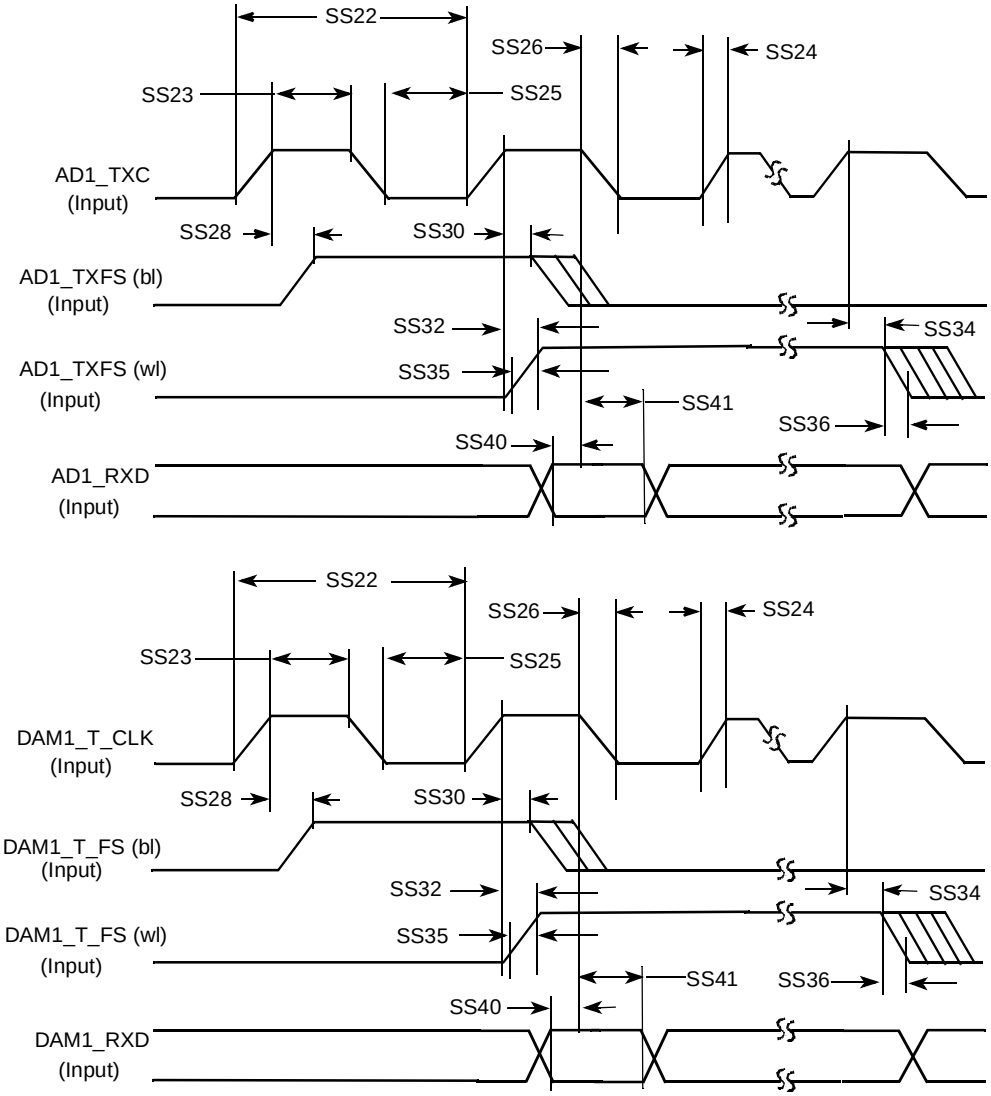


Figure 83. SSI Receiver with External Clock Timing Diagram

Table 62. SSI Receiver with External Clock Timing Parameters

ID	Parameter	Min	Max	Unit
External Clock Operation				
SS22	(Tx/Rx) CK clock period	81.4	—	ns
SS23	(Tx/Rx) CK clock high period	36.0	—	ns
SS24	(Tx/Rx) CK clock rise time	—	6.0	ns
SS25	(Tx/Rx) CK clock low period	36.0	—	ns
SS26	(Tx/Rx) CK clock fall time	—	6.0	ns

Table 62. SSI Receiver with External Clock Timing Parameters (continued)

ID	Parameter	Min	Max	Unit
SS28	(Rx) CK high to FS (bl) high	–10.0	15.0	ns
SS30	(Rx) CK high to FS (bl) low	10.0	—	ns
SS32	(Rx) CK high to FS (wl) high	–10.0	15.0	ns
SS34	(Rx) CK high to FS (wl) low	10.0	—	ns
SS35	(Tx/Rx) External FS rise time	—	6.0	ns
SS36	(Tx/Rx) External FS fall time	—	6.0	ns
SS40	SRXD setup time before (Rx) CK low	10.0	—	ns
SS41	SRXD hold time after (Rx) CK low	2.0	—	ns

4.3.23 USB Electrical Specifications

This section describes the electrical information of the USBOTG port. The OTG port supports both serial and parallel interfaces.

The high speed (HS) interface is supported via the ULPI (Ultra Low Pin Count Interface). Figure 84 depicts the USB ULPI timing diagram, and Table 63 lists the timing parameters.

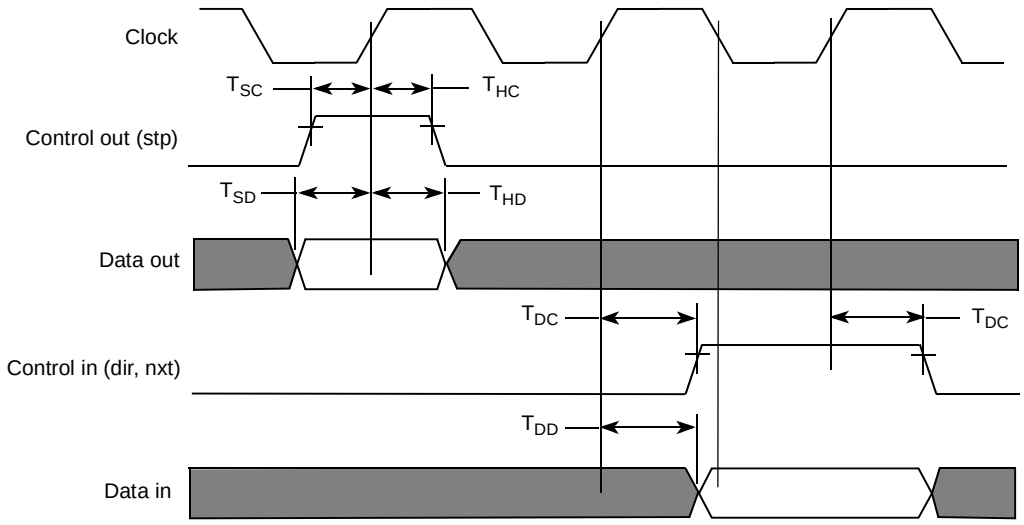


Figure 84. USB ULPI Interface Timing Diagram

Table 63. USB ULPI Interface Timing Specification[1]

Parameter	Symbol	Min	Max	Units
Setup time (control in, 8-bit data in)	T_{SC}, T_{SD}	6	—	ns
Hold time (control in, 8-bit data in)	T_{HC}, T_{HD}	0	—	ns
Output delay (control out, 8-bit data out)	T_{DC}, T_{DD}	—	9	ns

1 Timing parameters are given as viewed by transceiver side.

Table 65. 14 x 14 BGA Signal ID by Ball Grid Location (continued)

Signal ID	Ball Location
CSPI3_SCLK	E1
CSPI3_SPI_RDY	G6
CTS1	B11
CTS2	G13
D0	AB2
D1	Y3
D10	Y1
D11	U7
D12	W2
D13	V3
D14	W1
D15	U6
D2	AB1
D3	W6
D3_CLS	R20
D3_REV	T26
D3_SPL	U25
D4	AA2
D5	V7
D6	AA1
D7	W3
D8	Y2
D9	V6
DCD_DCE1	B12
DCD_DTE1	B13
$\overline{DE}$	C18
DQM0	AE19
DQM1	AD19
DQM2	AA20
DQM3	AE18
DRDY0	N26
DSR_DCE1	A11
DSR_DTE1	A12
DTR_DCE1	C11
DTR_DCE2	F12
DTR_DTE1	C12
DVFS0	E25
DVFS1	G24
EB0	W21
EB1	Y24
ECB	AD23
FPSHIFT	N21
GPIO1_0	F18
GPIO1_1	B23
GPIO1_2	C20
LD7	W25

Signal ID	Ball Location
GPIO1_3	F25
GPIO1_4	F19
GPIO1_5 (PWR RDY)	B24
GPIO1_6	A23
GPIO3_0	K21
GPIO3_1	H26
HSYNC	N25
I2C_CLK	J24
I2C_DAT	H25
IOIS16	J3
KEY_COL0	C15
KEY_COL1	B17
KEY_COL2	G15
KEY_COL3	A17
KEY_COL4	C16
KEY_COL5	B18
KEY_COL6	F15
KEY_COL7	A18
KEY_ROW0	F13
KEY_ROW1	B15
KEY_ROW2	C14
KEY_ROW3	A15
KEY_ROW4	G14
KEY_ROW5	B16
KEY_ROW6	F14
KEY_ROW7	A16
L2PG	See VPG1
LBA	AE22
LCS0	P26
LCS1	P21
LD0	T24
LD1	U26
LD10	V24
LD11	Y25
LD12	Y26
LD13	V21
LD14	AA25
LD15	W24
LD16	AA26
LD17	V20
LD2	T21
LD3	V25
LD4	T20
LD5	V26
LD6	U24
SCK6	T2

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